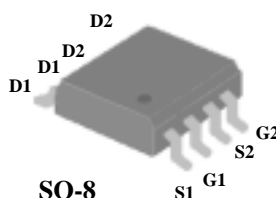




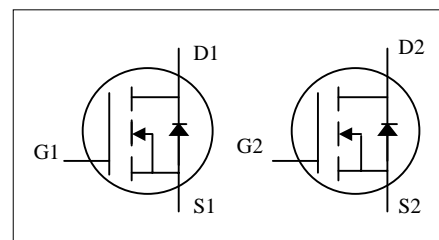
- ▼ Low Gate Charge
- ▼ Single Drive Requirement
- ▼ Surface Mount Package



$BV_{DSS}$	60V
$R_{DS(ON)}$	80m $\Omega$
$I_D$	3.9A

## Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, lower on-resistance and cost-effectiveness.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current <sup>3</sup> , $V_{GS} @ 10V$	3.9	A
$I_D @ T_A = 100^\circ C$	Continuous Drain Current <sup>3</sup> , $V_{GS} @ 10V$	2.5	A
$I_{DM}$	Pulsed Drain Current <sup>1,2</sup>	20	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 62.5	$^\circ C/W$



# AP9973M

## Electrical Characteristics @T<sub>j</sub>=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.06	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.9A	-	-	80	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	-	100	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3.9A	-	3.5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> = ± 20V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =3.9A	-	8	13	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =48V	-	2	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	4	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =30V	-	8	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	4	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	20	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =30Ω	-	6	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	700	1120	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	80	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	50	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =3.9A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =3.9A, V <sub>GS</sub> =0V, dI/dt=100A/μs	-	28	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	35	-	nC

### Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse width ≤300us, duty cycle ≤2%.
3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board; 135°C/W when mounted on min. copper pad.

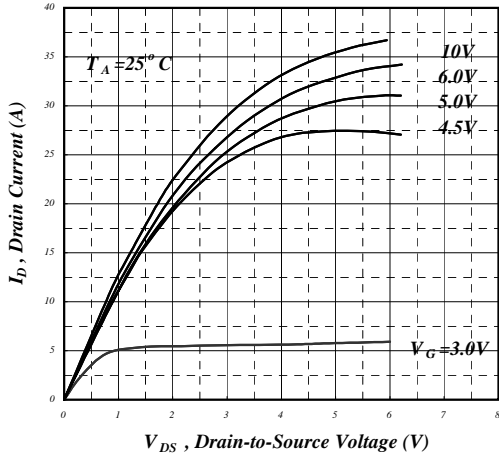


Fig 1. Typical Output Characteristics

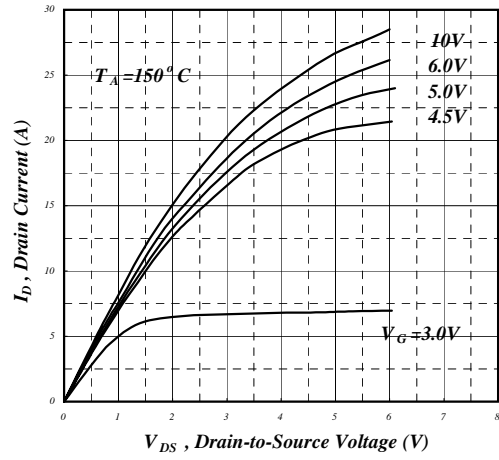


Fig 2. Typical Output Characteristics

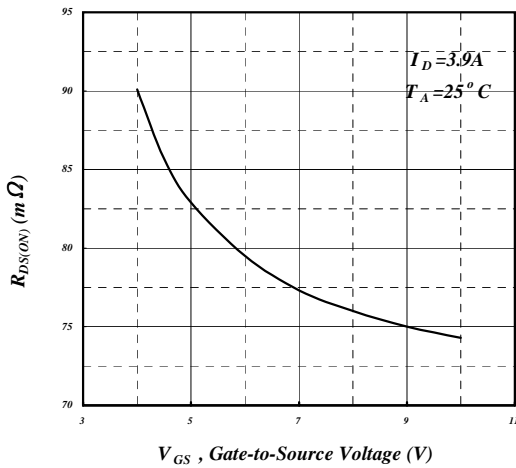


Fig 3. On-Resistance v.s. Gate Voltage

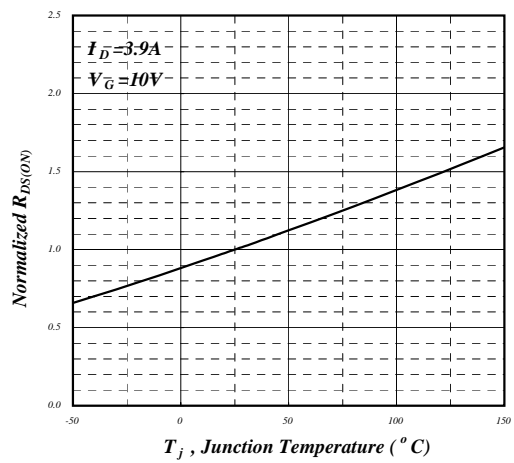


Fig 4. Normalized On-Resistance v.s. Junction Temperature

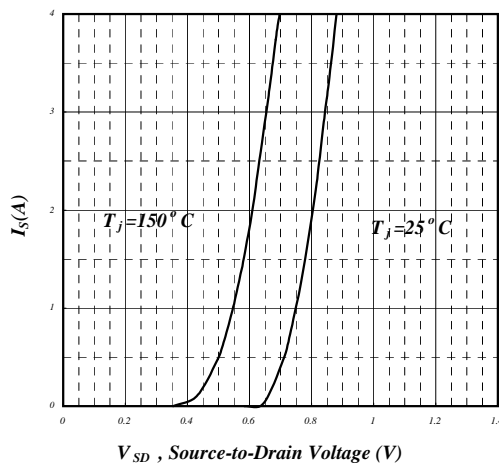


Fig 5. Forward Characteristic of Reverse Diode

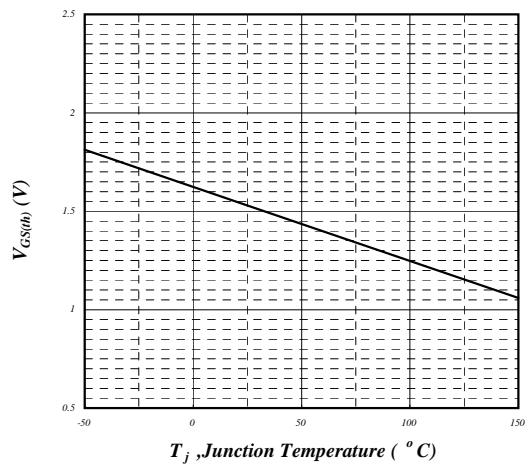


Fig 6. Gate Threshold Voltage v.s. Junction Temperature